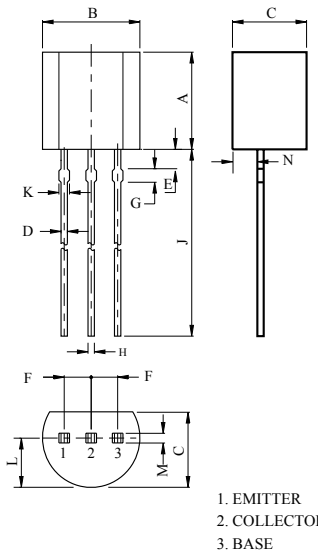
KTD1882

EPITAXIAL PLANAR NPN TRANSISTOR

AUDIO FREQUENCY POWER AMPLIFIER
LOW SPEED SWITCHING

FEATURES

· Complementary to KTB1772.



DIM	MILLIMETERS
A	4.70 MAX
B	4.80 MAX
C	3.70 MAX
D	0.45
E	1.00
F	1.27
G	0.85
H	0.45
J	14.00±0.50
K	0.55 MAX
L	2.30
M	0.45 MAX
N	1.00

1. EMITTER
2. COLLECTOR
3. BASE

TO-92

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	40	V
Collector-Emitter Voltage		V_{CEO}	30	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current	DC	I_C	3	A
	Pulse (Note)	I_{CP}	7	
Base Current (DC)		I_B	0.6	A
Collector Power Dissipation		P_C	625	mW
Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	-55～150	℃

Note : Pulse Width ≦10mS, Duty Cycle≦50%.

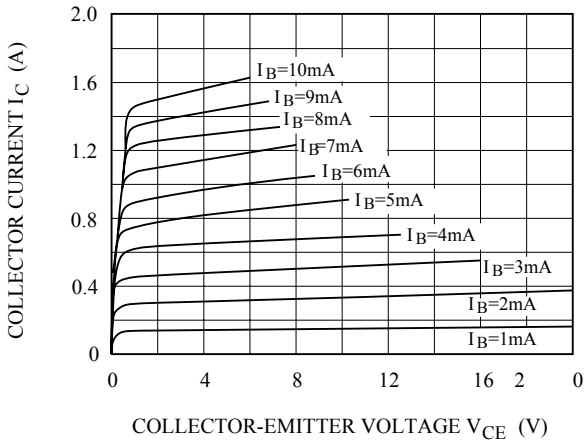
ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=30V, I_E=0	-	-	1	μA
Emitter-Cut-off Current	I_{EBO}	V_{EB}=3V, I_C=0	-	-	1	μA
DC Current Gain *	h_{FE}(1)	V_{CE}=2V, I_C=20mA	30	150	-	
	h_{FE}(2) (Note)	V_{CE}=2V, I_C=1A	100	160	400	
Collector-Emitter Saturation Voltage *	$V_{CE(sat)}$	I_C=2A, I_B=0.2A	-	0.3	0.5	V
Base-Emitter Saturation Voltage *	$V_{BE(sat)}$	I_C=2V, I_B=0.2A	-	1.0	2.0	V
Current Gain Bandwidth Product	f_T	V_{CE}=5V, I_C=0.1A	-	90	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz	-	45	-	pF

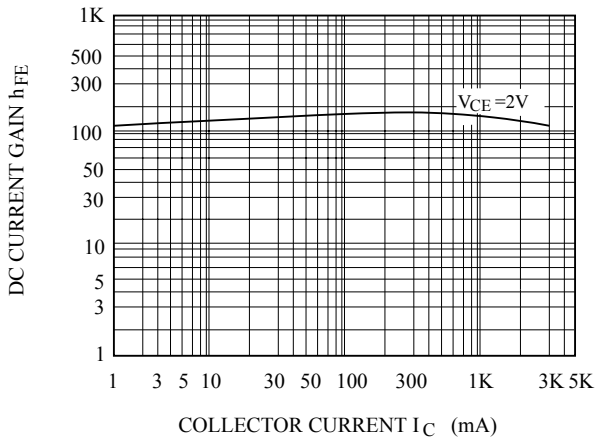
* Pulse Test : Pulse Width≤350μS, Duty Cycle≤2% Pulsed

Note: h_{FE}(2) Classification O:100～200 , Y:160～320 , GR:200～400

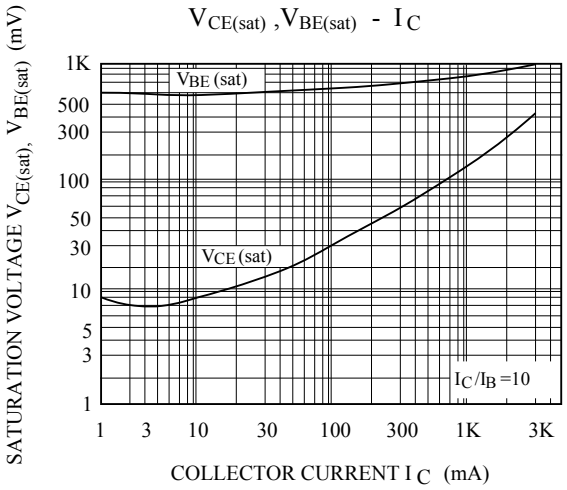
I_C - V_{CE}



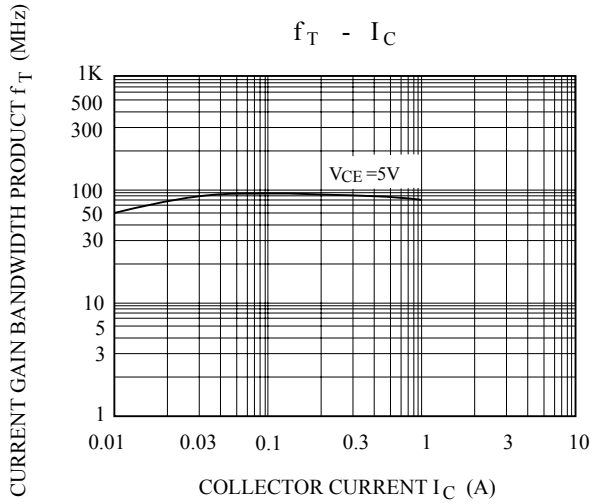
h_{FE} - I_C



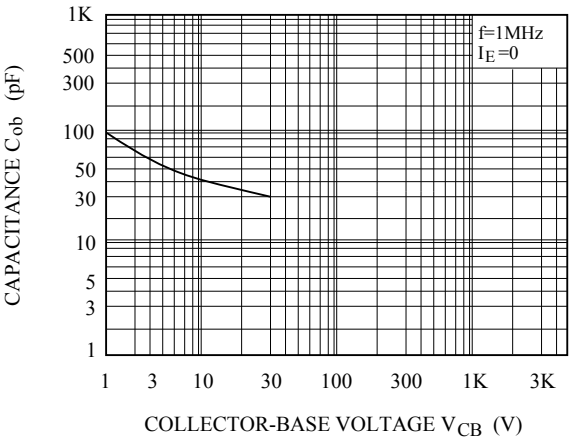
$V_{CE(sat)}$,$V_{BE(sat)}$ - I_C



f_T - I_C



C_{ob} - V_{CB}



P_C - Ta